

**FC806** 

Silicon Schottky Barrier Diode

# 50V, 100mA Rectifier

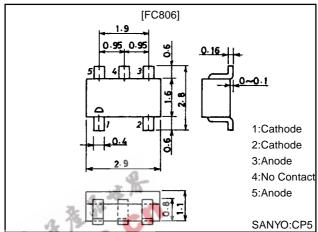
## **Features**

- · Low forward voltage ( $V_F$  max=0.55V).
- · Fast reverse recorvery time (trr max=10ns).
- · Composite type with 2 diodes contained in the CP package currently in use, saving the mounting space greatly.
- The FC806 is formed with two chips, each being equivalent to the SB01–05CP, placed in one package.

# **Package Dimensions**

unit:mm

1236A



# **Specifications**

## Absolute Maximum Ratings at Ta = 25°C

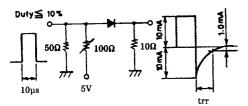
|  | _                |                          |             |      |
|--|------------------|--------------------------|-------------|------|
| Parameter                                | Symbol           | Conditions               | Ratings     | Unit |
| Repetitive Peak Reverse Voltage          | V <sub>RRM</sub> |                          | 50          | V    |
| Nonrepetitive Peak Reverse Surge Voltage | <sup>V</sup> RSM |                          | 55          | V    |
| Average Output Current                   | 10               |                          | 100         | mA   |
| Surge Forward Current                    | IFSM             | 50MHz sine wave, 1 cycle | 2           | Α    |
| Junction Temperature                     | Tj               |                          | -55 to +125 | °C   |
| Storage Temperature                      | Tstg             |                          | -55 to +125 | °C   |

### Electrical Characteristics at Ta = 25°C

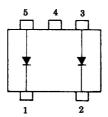
| Parameter                | Symbol         | Conditions  | Ratings |     |      | Unit |
|--------------------------|----------------|---|---------|-----|------|------|
|                          |                |   | min     | typ | max  |      |
| Reverse Voltage          | ٧ <sub>R</sub> | I <sub>R</sub> =50μA  | 50      |     |      | V    |
| Forward Voltage          | ٧F             | I <sub>F</sub> =100mA   |         |     | 0.55 | V    |
| Reverse Current          | IR             | V <sub>R</sub> =25V   |         |     | 15   | μA   |
| Interteminal Capacitance | С              | V <sub>R</sub> =10V, f=1MHz                                       |         | 4.4 |      | pF   |
| Reverse Recovery Time    | trr            | I <sub>F</sub> =I <sub>R</sub> =100mA, See specified Test Circuit |         |     | 10   | ns   |
| Thermal Resistance       | Rth (j-a)      |   |         | 560 |      | °C/W |

#### · Marking:806

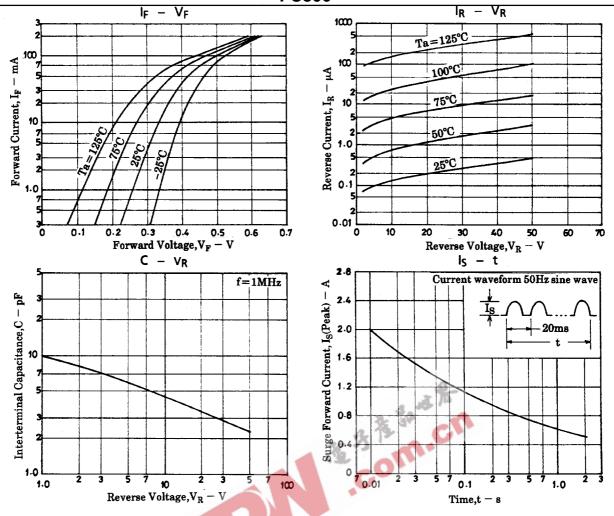
### trr Test Circuit



#### **Electrical Connection**



#### **FC806**



- No products described or contained herein are intended for use in surgical implants, life-support systems, aerospace equipment, nuclear power control systems, vehicles, disaster/crime-prevention equipment and the like, the failure of which may directly or indirectly cause injury, death or property loss.
- Anyone purchasing any products described or contained herein for an above-mentioned use shall:
  - ① Accept full responsibility and indemnify and defend SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors and all their officers and employees, jointly and severally, against any and all claims and litigation and all damages, cost and expenses associated with such use:
  - ② Not impose any responsibilty for any fault or negligence which may be cited in any such claim or litigation on SANYO ELECTRIC CO., LTD., its affiliates, subsidiaries and distributors or any of their officers and employees jointly or severally.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. SANYO believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

This catalog provides information as of February, 1998. Specifications and information herein are subject to change without notice.